RoHS COMPLIANT

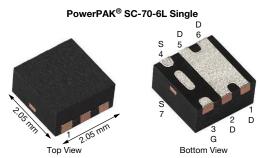
HALOGEN

FREE

www.vishay.com

Vishay Siliconix

P-Channel 20 V (D-S) MOSFET



Marking code: BQ

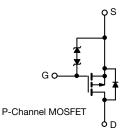
PRODUCT SUMMARY									
V _{DS} (V)	-20								
$R_{DS(on)}$ max. (Ω) at $V_{GS} = -4.5 \text{ V}$	0.0165								
$R_{DS(on)}$ max. (Ω) at $V_{GS} = -3.7 \text{ V}$	0.0185								
$R_{DS(on)}$ max. (Ω) at $V_{GS} = -2.5 \text{ V}$	0.0300								
Q _g typ. (nC)	23								
I _D (A) ^a	-12								
Configuration	Single								

FEATURES

- TrenchFET® power MOSFET
- Thermally enhanced PowerPAK SC-70 package
 - Small footprint area
 - Low on-resistance
- 100 % R_a tested
- · Built in ESD protection with Zener diode
- Typical ESD performance: 2000 V
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

APPLICATIONS

- · Smart phones, tablet PCs, mobile computing
 - Battery switch
 - Charger switch
 - Load switch



ORDERING INFORMATION	
Package	PowerPAK SC-70
Lead (Pb)-free and halogen-free	SiA445EDJ-T1-GE3

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)								
PARAMETER		SYMBOL	LIMIT	UNIT				
Drain-source voltage		V _{DS}	-20	V				
Gate-source voltage		V _{GS}	± 12	v				
	T _C = 25 °C		-12 ^a					
Continuous dusin surrent (T. 150 °C)	T _C = 70 °C	1 , [-12 ^a					
Continuous drain current (T _J = 150 °C)	T _A = 25 °C	l _D	-11.8 ^{b, c}					
	T _A = 70 °C		-9.5 ^{b, c}	Α				
Pulsed drain current (t = 300 μs)		I _{DM}	I _{DM} -50					
Ocalia a cara a data dia kacamat	T _C = 25 °C		-12 ^a					
Continuous source-drain diode current	T _A = 25 °C	ls ls	-2.9 ^{b, c}					
	T _C = 25 °C		19					
Maximum power dissipation	T _C = 70 °C		12	w				
	T _A = 25 °C	P _D	3.5 b, c	VV				
	T _A = 70 °C		2.2 b, c					
Operating junction and storage temperature rai	T _J , T _{stg}	-55 to +150	°C					
Soldering recommendations (peak temperature		260						

THERMAL RESISTANCE RATINGS								
PARAMETER	SYMBOL	TYPICAL	MAXIMUM	UNIT				
Maximum junction-to-ambient b, f	t ≤ 5 s	R_{thJA}	28	36	°C/W			
Maximum junction-to-case (drain)	Steady state	R_{thJC}	5.3	6.5	G/W			

- a. Package limited
- b. Surface mounted on 1" x 1" FR4 board
- t = 5 s
- d. See solder profile (www.vishay.com/doc?73257). The PowerPAK SC-70-6L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components
- f. Maximum under steady state conditions is 80 °C/W



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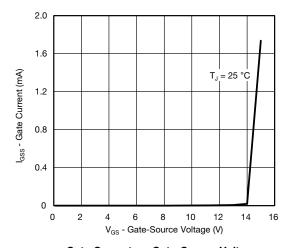
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static	<u> </u>		L		L	L
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	-20	-	-	V
V _{DS} temperature coefficient	$\Delta V_{DS}/T_{J}$	e/T ₁		-13	-	1400
V _{GS(th)} temperature coefficient	ΔV _{GS(th)} /T _J	I _D = -250 μA	-	2.6	-	mV/°C
Gate-source threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = -250 \mu A$	-0.5	-	-1.2	V
0-1	_	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$	-	-	± 60	
Gate-source leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 4.5 \text{ V}$	-	-	± 1	
7		V _{DS} = -20 V, V _{GS} = 0 V	-	-	-1	μΑ
Zero gate voltage drain current	I _{DSS}	$V_{DS} = -20 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$	-	-	-10	
On-state drain current ^a	I _{D(on)}	$V_{DS} \le -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	-20	-	-	Α
	. ,	$V_{GS} = -4.5 \text{ V}, I_D = -7 \text{ A}$	-	0.0135	0.0165	
Drain-source on-state resistance ^a	R _{DS(on)}	$V_{GS} = -3.7 \text{ V}, I_D = -5 \text{ A}$	-	0.0150	0.0185	Ω
		$V_{GS} = -2.5 \text{ V}, I_D = -5 \text{ A}$	-	0.0210	0.0300	
Forward transconductance ^a	9 _{fs}	V _{DS} = -10 V, I _D = -7 A	-	29	-	S
Dynamic ^b						
Input capacitance	C _{iss}		-	2130	-	pF
Output capacitance	C _{oss}	$V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	-	290	-	
Reverse transfer capacitance	C _{rss}		-	280	-	
Total gate charge	0	$V_{DS} = -10 \text{ V}, V_{GS} = -10 \text{ V}, I_D = -12 \text{ A}$	-	48	72	nC
	Q_g Q_gs		-	23	35	
Gate-source charge		$V_{DS} = -10 \text{ V}, V_{GS} = -4.5 \text{ V}, I_D = -12 \text{ A}$	-	3.1	-	
Gate-drain charge	Q _{gd}		-	6.7	-	
Gate resistance	R_g	f = 1 MHz	1.2	6	12	Ω
Turn-on delay time	t _{d(on)}		-	25	50	
Rise time	t _r	V_{DD} = -10 V, R_L = 1 Ω	-	25	50	
Turn-off delay time	t _{d(off)}	$I_D\cong$ -9.5 A, V_{GEN} = -4.5 V, R_g = 1 Ω	-	55	110	
Fall time	t _f		-	20	40	1
Turn-on delay time	t _{d(on)}		-	7	15	ns
Rise time	t _r	V_{DD} = -10 V, R_L = 1 Ω	-	10	20	- - -
Turn-off delay time	t _{d(off)}	$I_D\cong$ -9.5 A, $V_{GEN}=$ -10 V, $R_g=$ 1 Ω	-	60	120	
Fall time	t _f		-	17	35	
Drain-Source Body Diode Characterist	ics					
Continuous source-drain diode current	I _S	T _C = 25 °C	-	-	-12	^
Pulse diode forward current	I _{SM}		-	-	-50	Α
Body diode voltage	V_{SD}	$I_S = -9.5 \text{ A}, V_{GS} = 0 \text{ V}$	-	-0.8	-1.2	V
Body diode reverse recovery time	t _{rr}		-	15	30	ns
Body diode reverse recovery charge	Q _{rr}	$I_F = -9.5 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s},$	-	5	10	nC
Reverse recovery fall time	t _a	T _J = 25 °C	-	7	-	
Reverse recovery rise time	t _b		-	8	-	ns

Notes

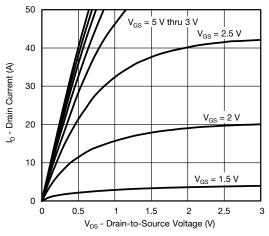
- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %
- b. Guaranteed by design, not subject to production testing

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

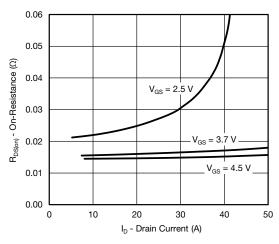




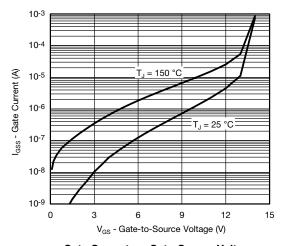
Gate Current vs. Gate-Source Voltage



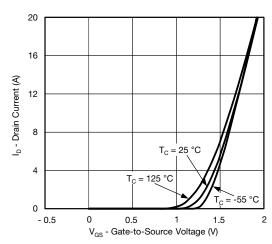
Output Characteristics



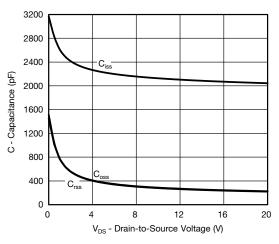
On-Resistance vs. Drain Current



Gate Current vs. Gate-Source Voltage

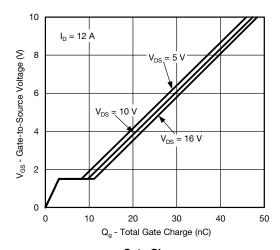


Transfer Characteristics

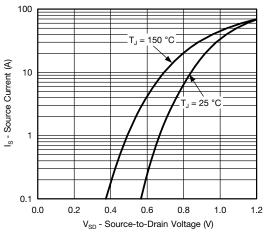


Capacitance

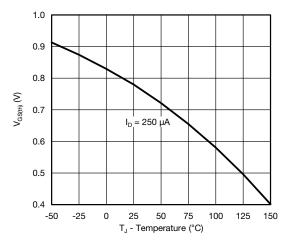




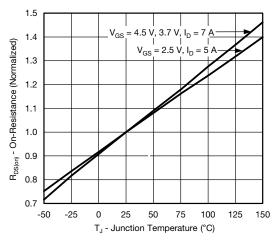
Gate Charge



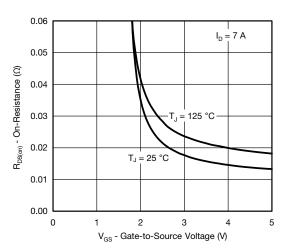
Source-Drain Diode Forward Voltage



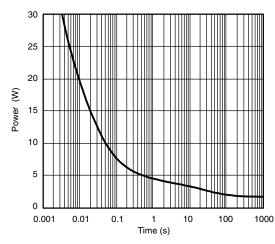
Threshold Voltage



On-Resistance vs. Junction Temperature

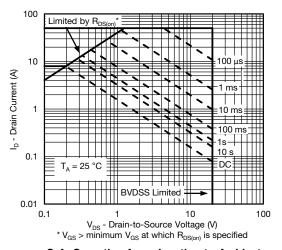


On-Resistance vs. Gate-to-Source Voltage

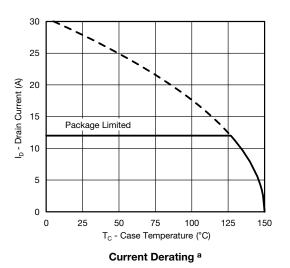


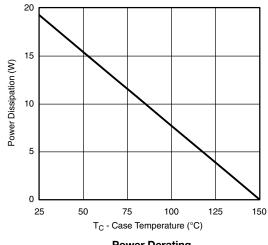
Single Pulse Power, Junction-to-Ambient





Safe Operating Area, Junction-to-Ambient



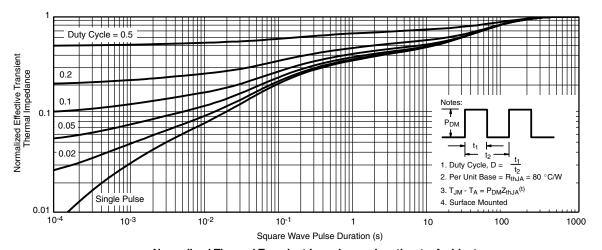


Power Derating

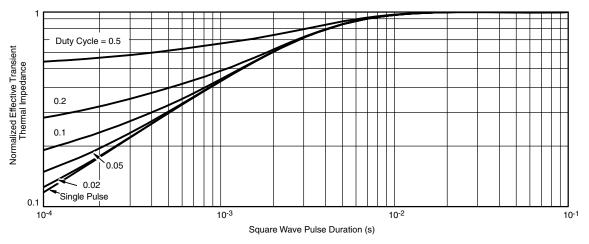
Note

a. The power dissipation P_D is based on T_J max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit





Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?63619.





Vishay Siliconix

PowerPAK® SC70-6L





BACKSIDE VIEW OF SINGLE

BACKSIDE VIEW OF DUAL



- All dimensions are in millimeters
 Package outline exclusive of mold flash and metal burr
 Package outline inclusive of plating

	SINGLE PAD						DUAL PAD					
DIM	M	ILLIMETER	RS	INCHES			MILLIMETERS			INCHES		
	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max
Α	0.675	0.75	0.80	0.027	0.030	0.032	0.675	0.75	0.80	0.027	0.030	0.032
A1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002
b	0.23	0.30	0.38	0.009	0.012	0.015	0.23	0.30	0.38	0.009	0.012	0.015
С	0.15	0.20	0.25	0.006	0.008	0.010	0.15	0.20	0.25	0.006	0.008	0.010
D	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085
D1	0.85	0.95	1.05	0.033	0.037	0.041	0.513	0.613	0.713	0.020	0.024	0.028
D2	0.135	0.235	0.335	0.005	0.009	0.013						
Е	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085
E1	1.40	1.50	1.60	0.055	0.059	0.063	0.85	0.95	1.05	0.033	0.037	0.041
E2	0.345	0.395	0.445	0.014	0.016	0.018						
E3	0.425	0.475	0.525	0.017	0.019	0.021						
е		0.65 BSC			0.026 BSC	;	0.65 BSC			0.026 BSC		
K		0.275 TYP			0.011 TYP		0.275 TYP			0.011 TYP		
K1		0.400 TYP		0.016 TYP		0.320 TYP			0.013 TYP			
K2		0.240 TYP		0.009 TYP		0.252 TYP			0.010 TYP			
К3		0.225 TYP		0.009 TYP					•	•		
K4		0.355 TYP		0.014 TYP								
L	0.175	0.275	0.375	0.007	0.011	0.015	0.175	0.275	0.375	0.007	0.011	0.015
T							0.05	0.10	0.15	0.002	0.004	0.006

ECN: C-07431 - Rev. C, 06-Aug-07

DWG: 5934

06-Aug-07



RECOMMENDED PAD LAYOUT FOR PowerPAK® SC70-6L Single



Dimensions in mm/(Inches)

Return to Index

ATTLICATION NOT



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